MICRO ELECTRONICS

PN3567

NPN SILICON TRANSISTOR

DESCRIPTION

PN3567 is NPN silicon planar epitaxial transistor designed for amplifier and switching applications.

TO-92

EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CBO}	80V
Collector-Emitter Voltage	V_{CEO}	60V
Emitter-Base Voltage	V_{EBO}	5V
Collector Current	I_C	500mA
Continuous Power Dissipation	P_d	600mW
Operating & Storage Junction Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV_{CBO}	80		V	I_C=100μA I_E=0
Collector-Emitter Breakdown Voltage	LV_{CEO}	40		V	I_C=10mA I_B=0*
Emitter-Base Breakdown Voltage	BV_{EBO}	5		V	I_E=10μA I_C=0
Collector Cutoff Current	I_{CBO}		50	nA	V_{CB}=40V I_E=0
D.C. Current Gain	H_{FE}	40			I_C=30mA V_{CE}=1V*
		40	120		I_C=150mA V_{CE}=1V*
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25	V	I_C=150mA I_B=15mA*
Output Capacitance	C_{ob}		20	pF	V_{CB}=10V f=1MHz
Current Gain-Bandwidth Product	f_T	60	600	MHz	I_C=50mA V_{CE}=1V

*Pulse Test : Pulse Width = 300μS, Duty Cycle = 2%.